SOT-23 Plastic-Encapsulate MOSFETS

Features

- V_{DS}= -20V
- I_D=-5.6A
- $R_{DS(on)}$@VGS=-4.5V ＜ 42mΩ
- $R_{DS(on)}$@VGS=-2.5V ＜ 55mΩ
- Trench Power MV MOSFET technology
- Voltage controlled small signal switch
- Fast Switching Speed

Drain-source Voltage
-20 V
Drain Current
-5.6 Ampere

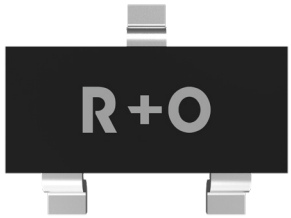
Applications

- Battery operated systems
- Solid-state relays
- Direct logic-level interface：TTL/CMOS

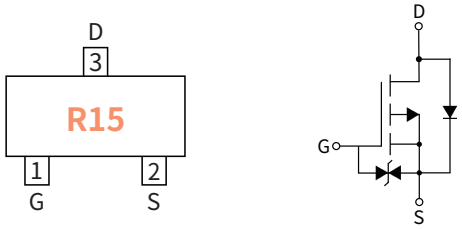
Mechanical Data

- Case: SOT-23
  Molding compound meets UL 94V-0 flammability rating, RoHS-compliant,halogen-free
- Terminals: Solder plated, solderable per MIL-STD-750,Method 2026

SOT-23



Reference News



Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	VALUE
Drain-source Voltage		V_{DS}	V	-20
Gate-source Voltage		V_{GS}	V	±12
Drain Current	T_A=25°C @ Steady State	I_D	A	-5.6
Pulsed Drain Current (1)		I_{DM}	A	-23
Total Power Dissipation @ T_A=25°C		P_D	W	1.3
ESD Protected Up to		ESD(HBM)	kV	2.0
Thermal Resistance Junction-to-Ambient @ Steady State (2)		$R_{\theta JA}$	°C / W	98
Junction and Storage Temperature Range		T_J,T_{STG}	°C	-55 ~+150

Note :

(1)The power dissipation PD is based on TJ(MAX)=150° C, using ≤ 10s junction-to-ambient thermal resistance.

Ordering Information

PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	45000	180000	7''

Static Parameter Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D= -250μA	V	-20	—	—
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= -20V,V_{GS}=0V	μA	—	—	-1.0
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±10V, V_{DS}=0V	μA	—	—	±15
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	V	-0.4	-0.62	-1.0
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}= -4.5V, I_D= -5.0A	mΩ	—	31	42
		V_{GS}= -2.5V, I_D= -4.0A		—	41	55
Forward Transconductance	gfs	V_{DS}= -5.0V, I_D= -4.0A	S	—	20	—
Diode Forward Voltage	V_{SD}	I_S= -5.0A,V_{GS}=0V	V	—	—	-1.2

Dynamic Parameters (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Input Capacitance	C_{iss}	V_{DS}=0V V_{DS}= -10V f=1MHZ	pF	—	1180	—
Output Capacitance	C_{oss}			—	125	—
Reverse Transfer Capacitance	C_{rss}			—	88	—

Switching Parameters (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	Condition	UNIT	Min	Typ	Max
Total Gate Charge	Q_g	V_{GS}= -4.5V V_{DS}= -10V I_D= -4.0A	nC	—	11	—
Gate-Source Charge	Q_{gs}			—	2.0	—
Gate-Drain Charge	Q_{gd}			—	3.0	—
Reverse Recovery Charge	Q_{rr}	I_F= -4.0A di/dt=100A/us		—	13.8	—
Reverse Recovery Time	t_{rr}		ns	—	31	—
Turn-on Delay Time	$t_{D(on)}$	V_{GS}= -4.5V V_{DS}= -10V I_D= -1.0A R_{GEN}=2.5Ω		—	14	—
Turn-on Rise Time	t_r			—	10	—
Turn-off Delay Time	$t_{D(off)}$			—	20	—
Turn-off fall Time	t_f			—	30	—

Ratings And Characteristics Curves (Ta=25°C Unless otherwise specified)

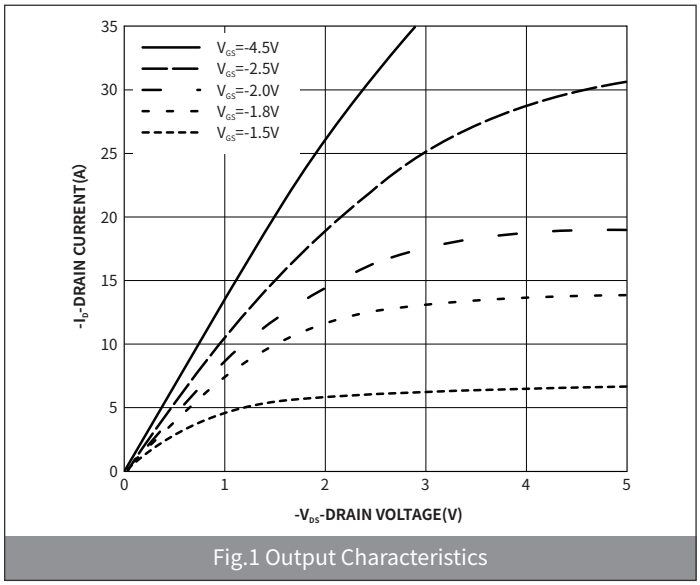


Fig.1 Output Characteristics

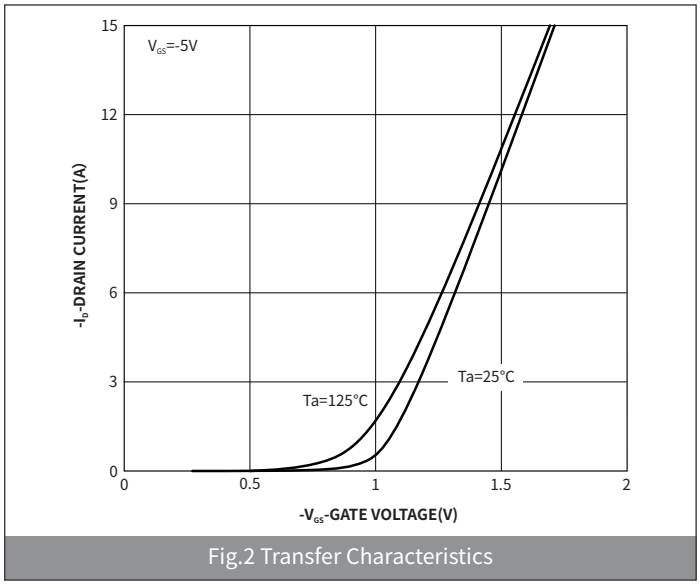


Fig.2 Transfer Characteristics

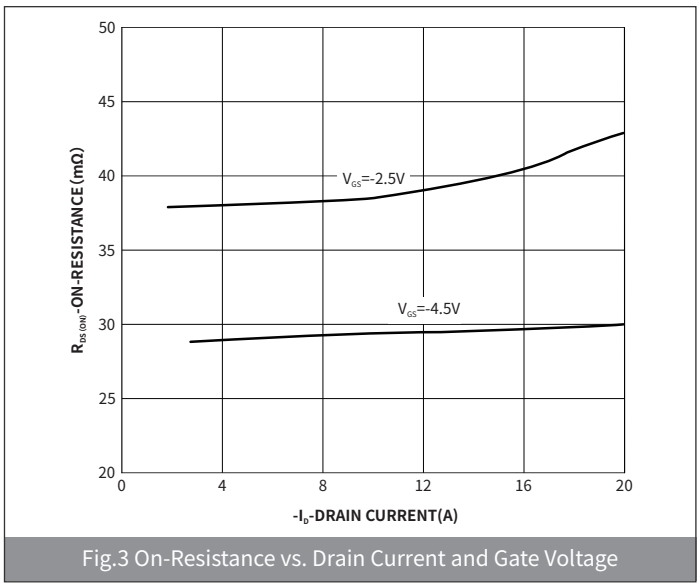


Fig.3 On-Resistance vs. Drain Current and Gate Voltage

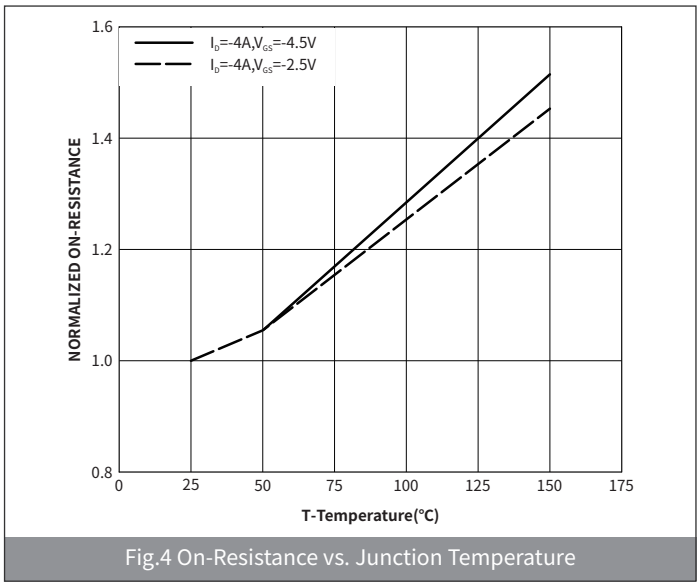


Fig.4 On-Resistance vs. Junction Temperature

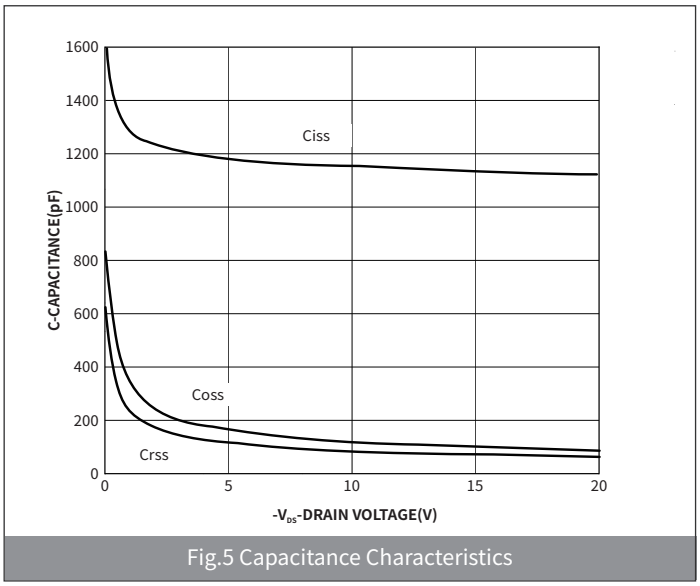


Fig.5 Capacitance Characteristics

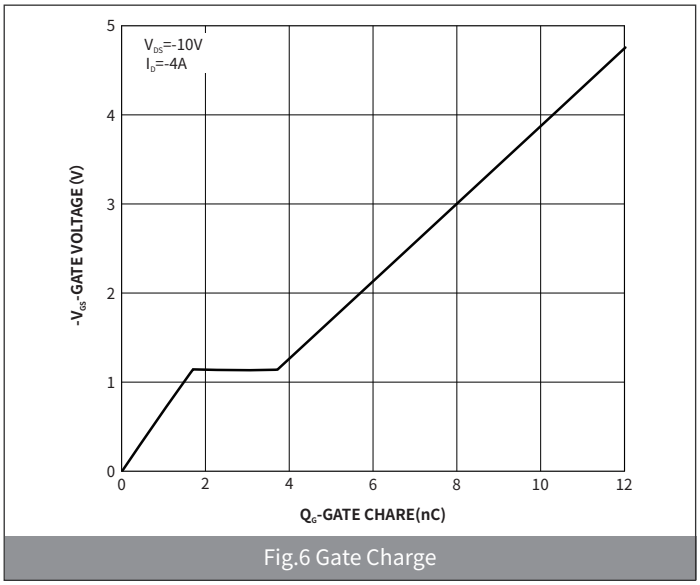


Fig.6 Gate Charge

Ratings And Characteristics Curves (Ta=25°C Unless otherwise specified)

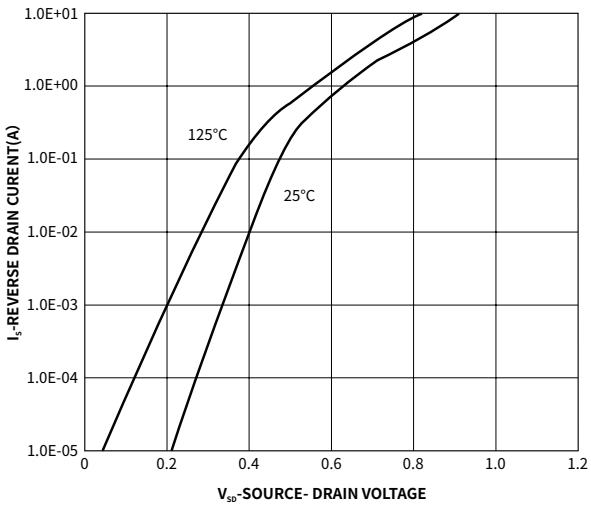


Fig.7 Diode Characteristics

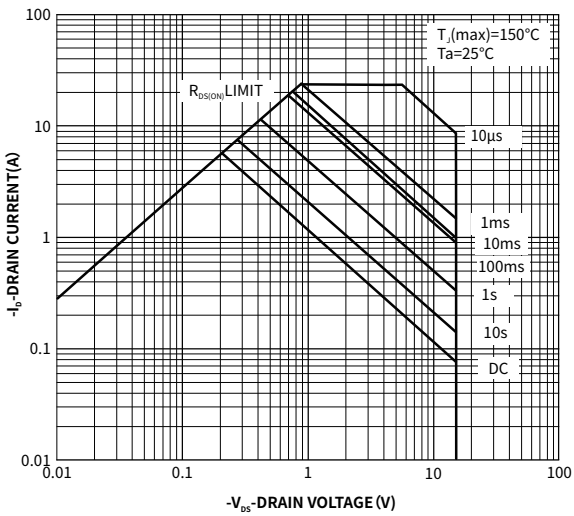


Fig.8 Safe Operation Area

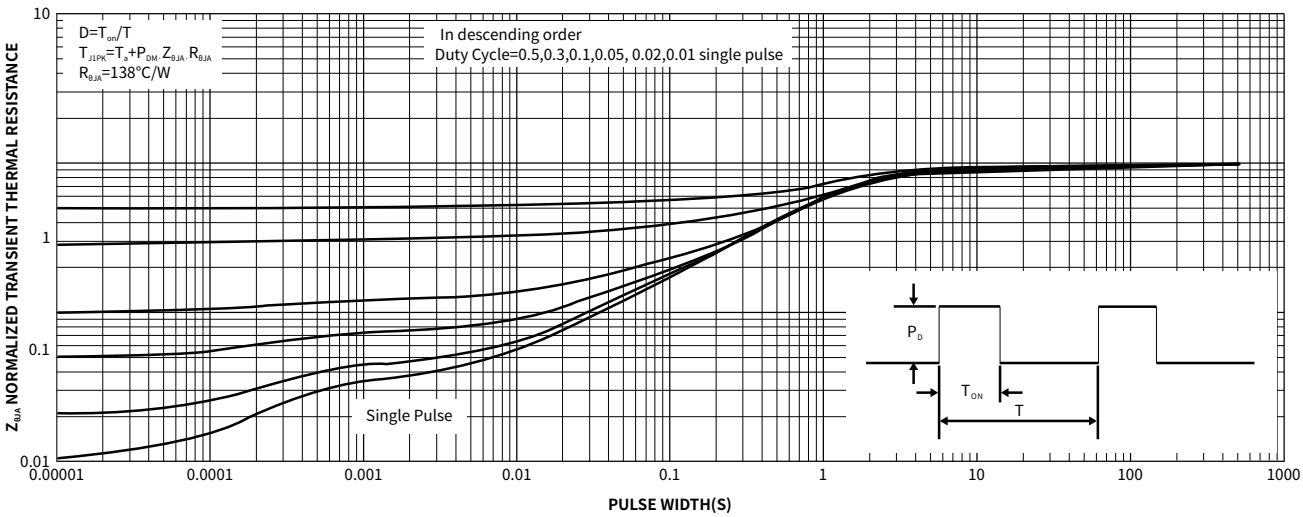
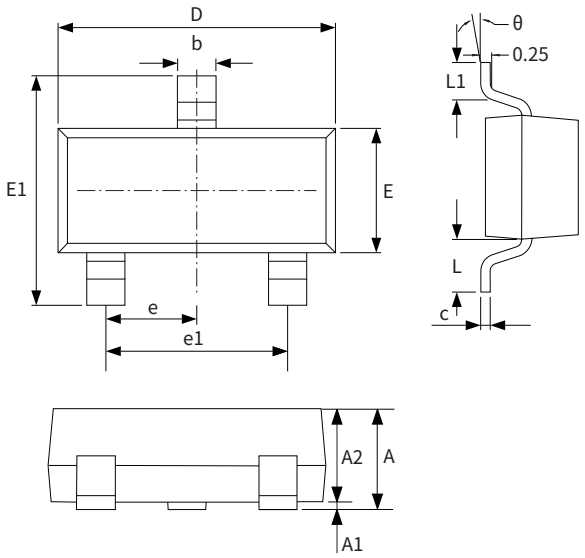


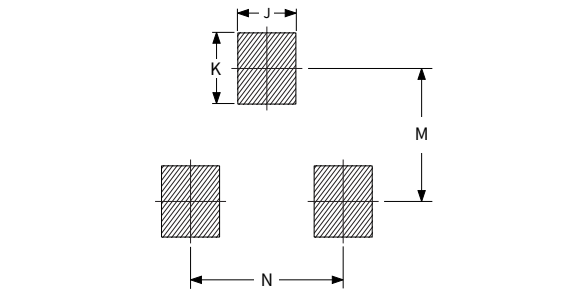
Fig.9 Normalized Maximum Transient Thermal Impedance

Package Outline Dimensions (SOT-23)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.80	-	0.031	-
K	-	0.90	-	0.035
M	2.00	-	0.078	-
N	-	1.90	-	0.074